PJQ4528P-AU

30V N-Channel Enhancement Mode MOSFET

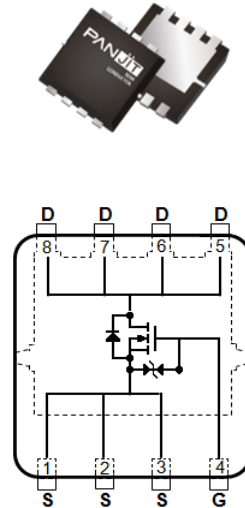| **Voltage** | **30 V** | **Current** | **55 A** |

DFN3333-8L

Features

- $R_{DS(ON)}$, V_{GS}@10V, I_D@12A<6.5mΩ
- $R_{DS(ON)}$, V_{GS}@4.5V, I_D@9A<10.5mΩ
- Excellent FOM
- Logic Level Drive
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case : DFN3333-8L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.03 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current[Note 3]	T_C=25°C	I_D	55	A
	T_C=100°C		39	
Pulsed Drain Current[Note 1]	T_C=25°C	I_{DM}	220	
Power Dissipation	T_C=25°C	P_D	32	W
	T_C=100°C		16	
Continuous Drain Current[Note 4]	T_A=25°C	I_D	15.5	A
	T_A=70°C		13	
Power Dissipation	T_A=25°C	P_D	2.5	W
	T_A=70°C		1.8	
Single Pulse Avalanche Energy[Note 5]		E_{AS}	44	mJ
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~175	^{o}C
Thermal Resistance[Note 4]	Junction to Case	$R_{\theta JC}$	4.7	^{o}C/W
	Junction to Ambient	$R_{\theta JA}$	60	

PJQ4528P-AU

Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.2	1.76	2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=12A	-	5.6	6.5	mΩ
		V_{GS}=4.5V, I_D=9A	-	8.3	10.5	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±10	uA
Dynamic[Note 6]						
Total Gate Charge	Q_g	V_{DS}=15V, I_D=12A, V_{GS}=10V[Note 2,3]	-	10.7	-	nC
Gate-Source Charge	Q_{gs}		-	2	-	
Gate-Drain Charge	Q_{gd}		-	2.2	-	
Input Capacitance	Ciss	V_{DS}=15V, V_{GS}=0V, f=1MHz	-	785	-	pF
Output Capacitance	Coss		-	375	-	
Reverse Transfer Capacitance	Crss		-	25	-	
Gate resistance	R_g	f=1MHz	-	2	-	Ω
Turn-On Delay Time	$td_{(on)}$	V_{DS}=15V, I_D=1A, V_{GS}=10V, R_G=1Ω (Note 2,3)	-	9	-	ns
Turn-On Rise Time	t_r		-	2	-	
Turn-Off Delay Time	$td_{(off)}$		-	20	-	
Turn-Off Fall Time	t_f		-	7	-	
Drain-Source Diode						
Diode Forward Current	I_S	T_C=25°C	-	-	55	A
Pulsed Diode Forward Current	I_{SM}		-	-	220	
Diode Forward Voltage	V_{SD}	I_S=10A, V_{GS}=0V	-	0.83	1.1	V
Reverse Recovery Time	Trr	V_{GS}=0V, I_S=10A	-	14	-	ns
Reverse Recovery Charge	Qrr	dI_S/dt=100A/us[Note 2,3]	-	13	-	nC

NOTES :

1. Pulse width≤100us, Duty cycle≤2%.
2. Essentially independent of operating temperature typical characteristics.
3. Chip capability with an $R_{\theta JC}$=4.7°C/W.
4. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch^2 with 2oz.square pad of copper.
5. The test condition is L=0.5mH, I_{AS}=13A, V_{DD}=30V, V_{GS}=10V, Starting TJ=25°C.
6. Guaranteed by design, not subject to production testing.
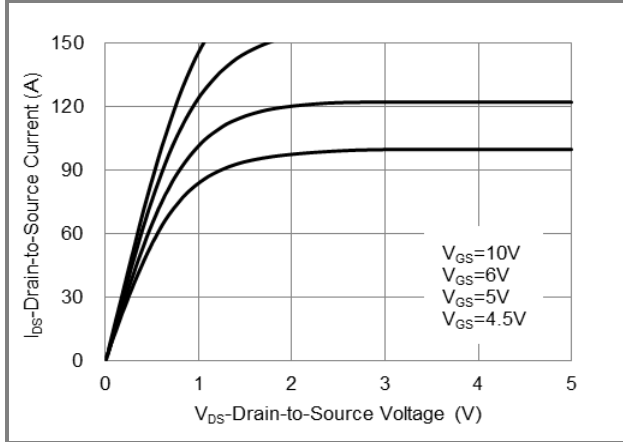
TYPICAL CHARACTERISTIC CURVES

Fig.1 On-Region Characteristics

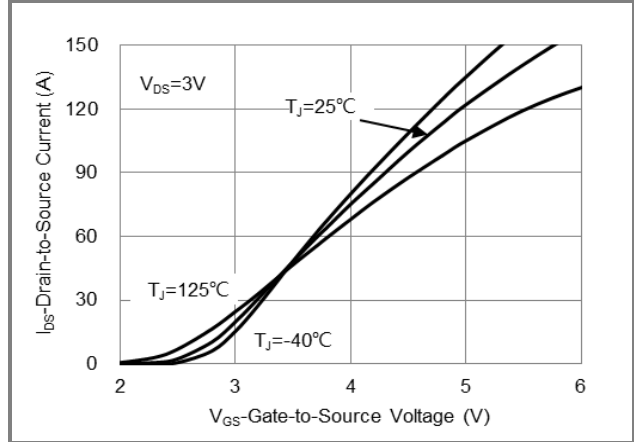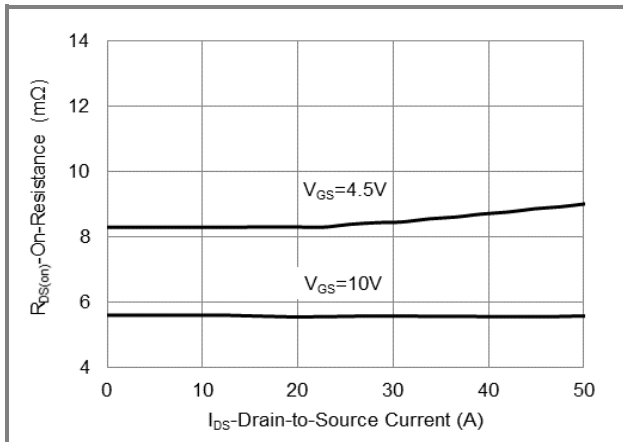**Fig.2 Transfer Characteristics**

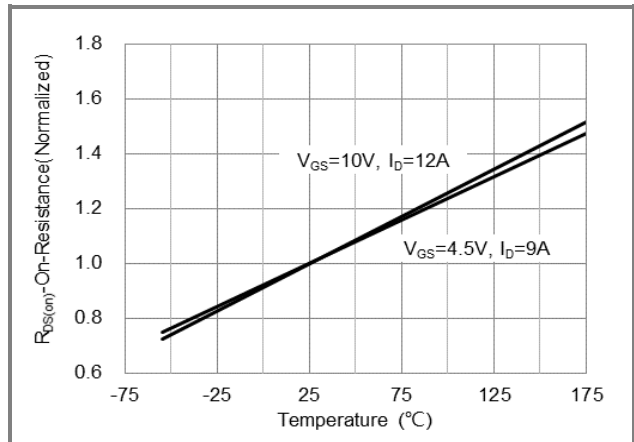**Fig.3 On-Resistance vs. Drain Current**

Fig.4 On-Resistance vs. Junction temperature
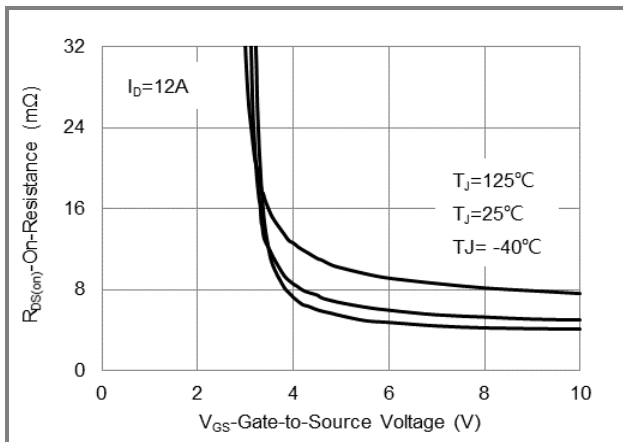
Fig.5 On-Resistance Variation with V_{GS}

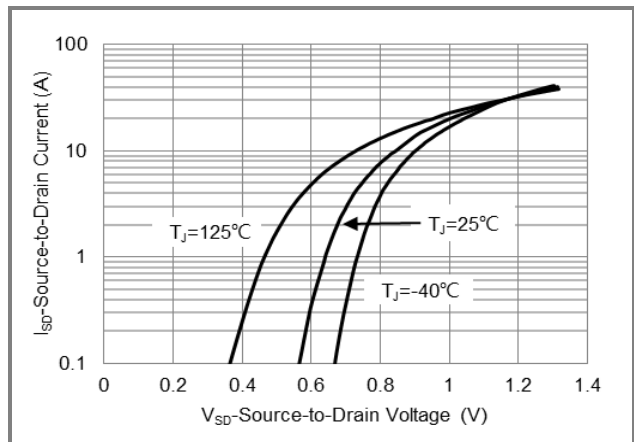**Fig.6 Source-Drain Diode Forward Voltage**
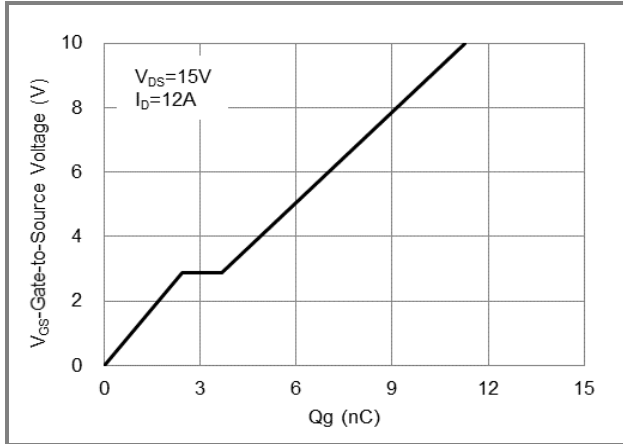
TYPICAL CHARACTERISTIC CURVES

$V_{DS}=15V$
$I_D=12A$

Fig.7 Gate-Charge Characteristics

$I_D=250uA$
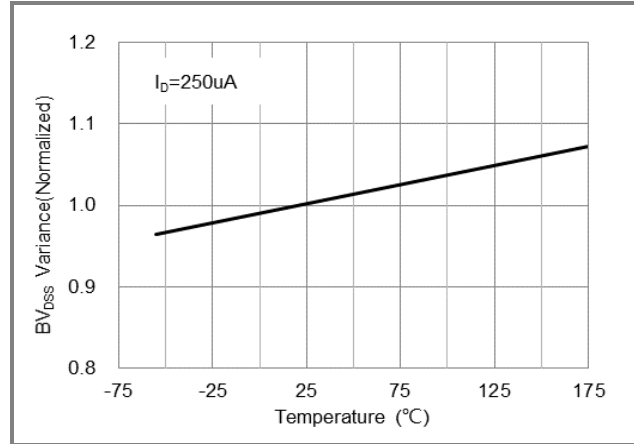
Fig.8 Breakdown Voltage Variation vs. Temperature

$I_D=250uA$
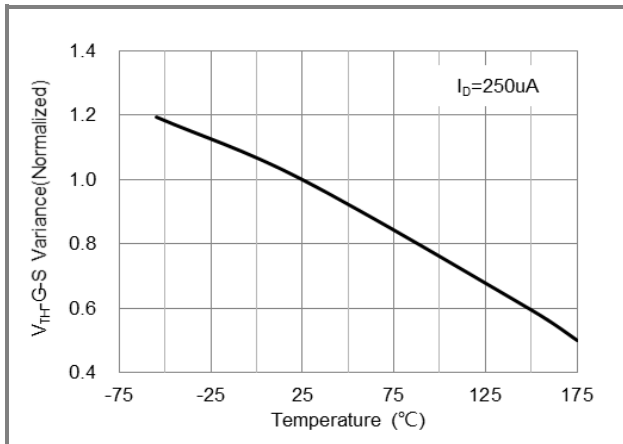
Fig.9 Threshold Voltage Variation with Temperature

$V_{GS}=0$
$f=1MHz$

C_{iss}

C_{oss}

C_{rss}
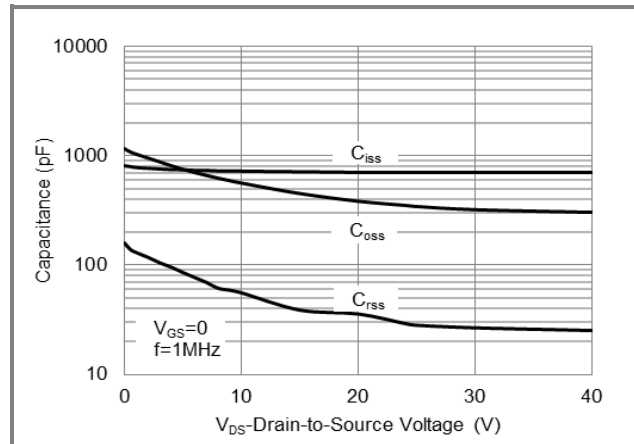
Fig.10 Capacitance vs. Drain-Source Voltage

Operation this area is Limited by $R_{DS(ON)}$

10us
100us
1ms
10ms
DC

Notes :
1. T_J=Max Rated
2. T_C=25℃
3. R_{THJ-C}=4.7℃/W
4. Single pulse
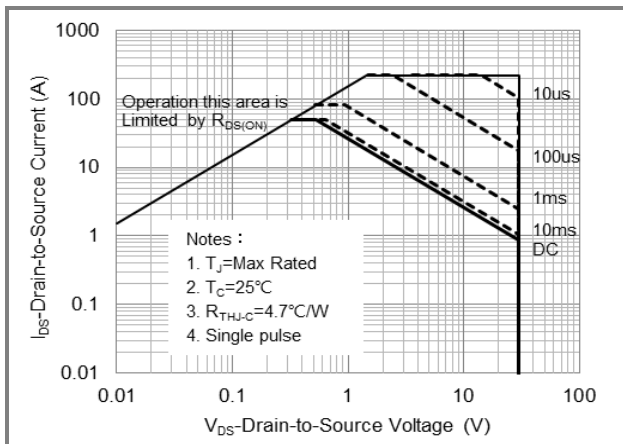
Fig.11 Maximum Safe Operating Area

D=0.5
0.2
0.1
0.05
0.02
0.01

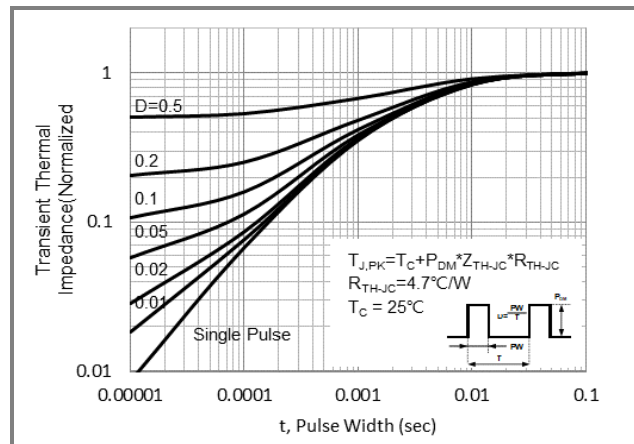$T_{J,PK}=T_C+P_{DM}*Z_{TH-JC}*R_{TH-JC}$
$R_{TH-JC}=4.7℃/W$
$T_C = 25℃$

Single Pulse

Fig.12 Normalized Transient Thermal Impedance

Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ4528P-AU	DFN3333-8L	5K pcs / 13" reel	4528

Packaging Information & Mounting Pad Layout

DFN3333-8L Dimension — Unit: inch(mm)

DFN3333-8L Pad Layout — Unit: inch(mm)
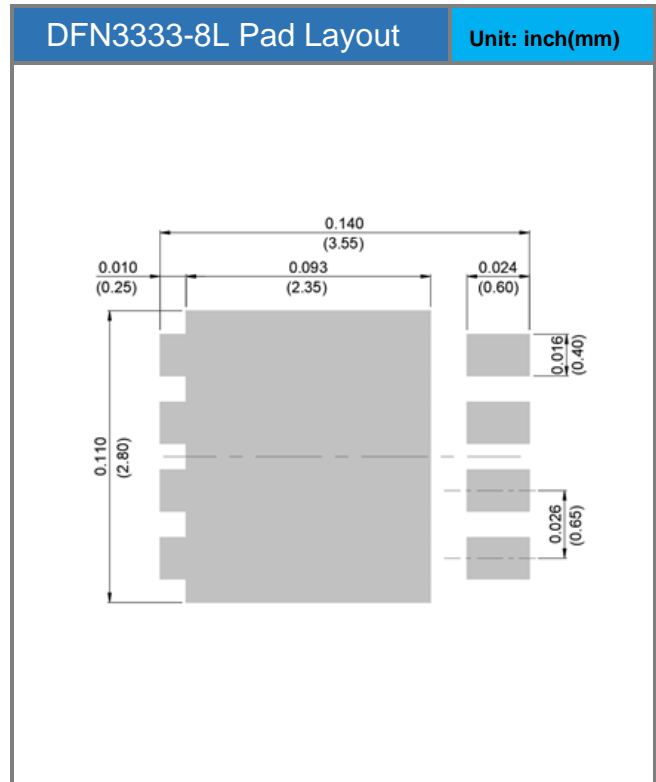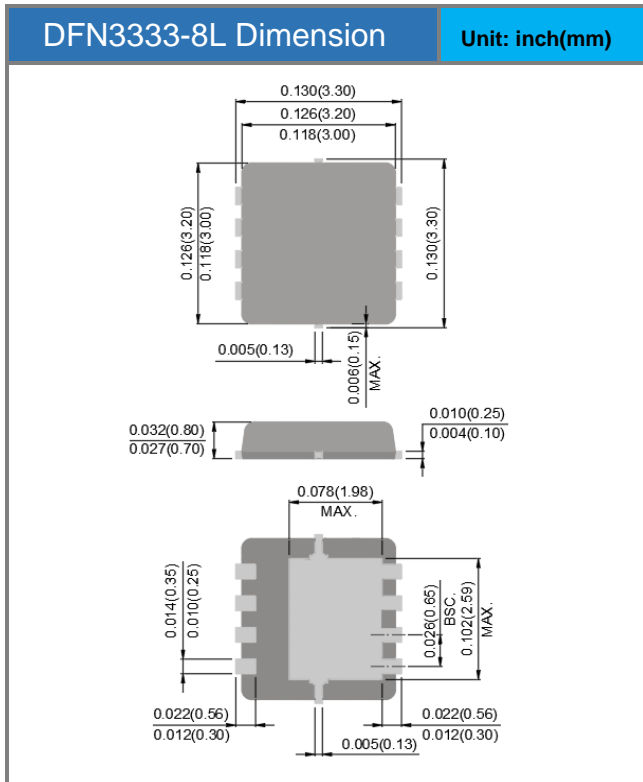
PJQ4528P-AU

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